



Static control in Ultrapure DI water application

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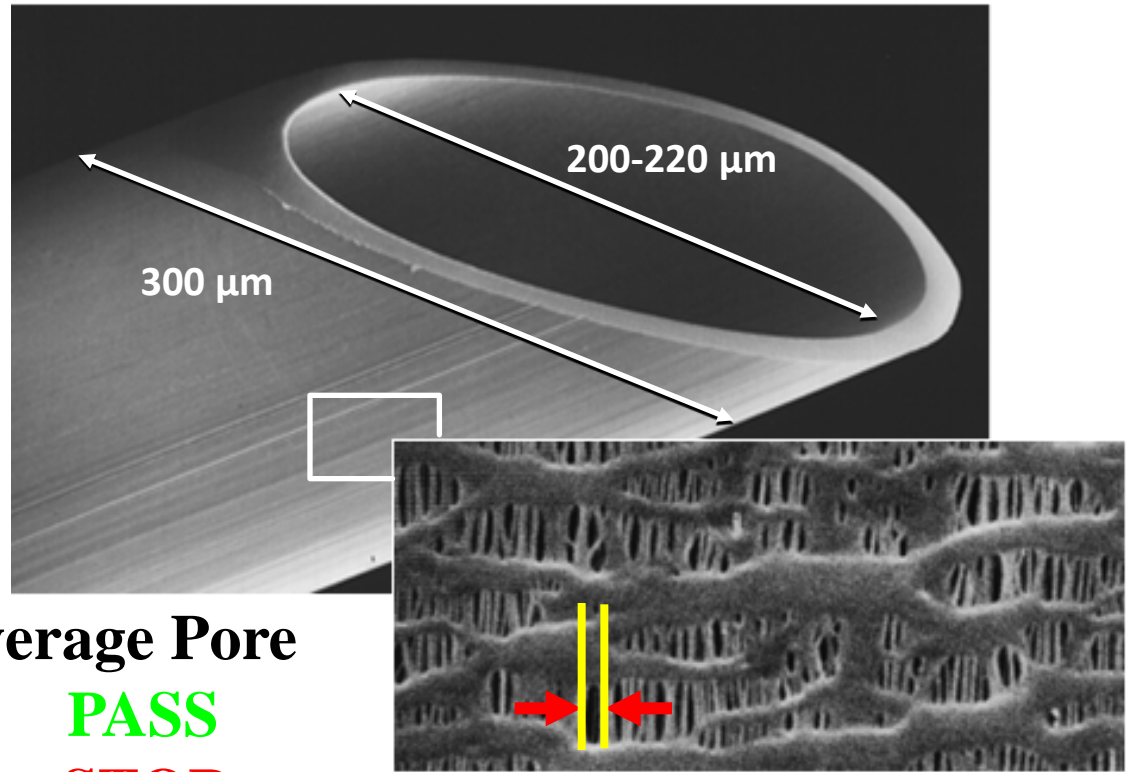
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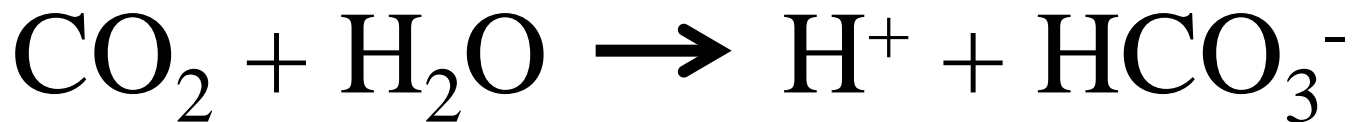
Outline

- Introduction
- System Design
- Results

Introduction



0.03 μm Average Pore
CO₂ gas **PASS**
H₂O liquid **STOP**





Industrial Applications

General surface cleaning

Wafer dicing process

Single substrate spin cleaning process

Biggest issue for DICO_2 process

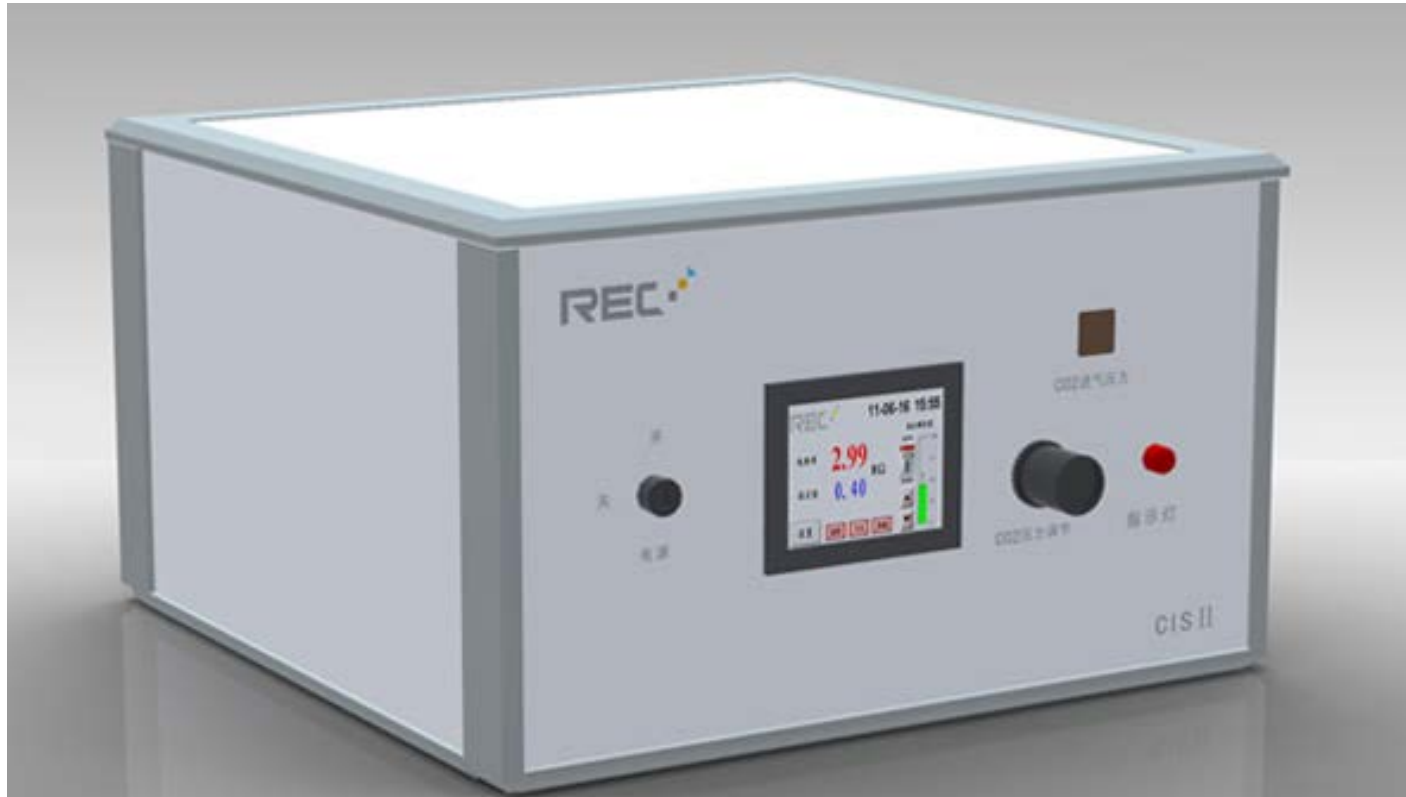
How to keep the conductivity set point with wide flowrate span

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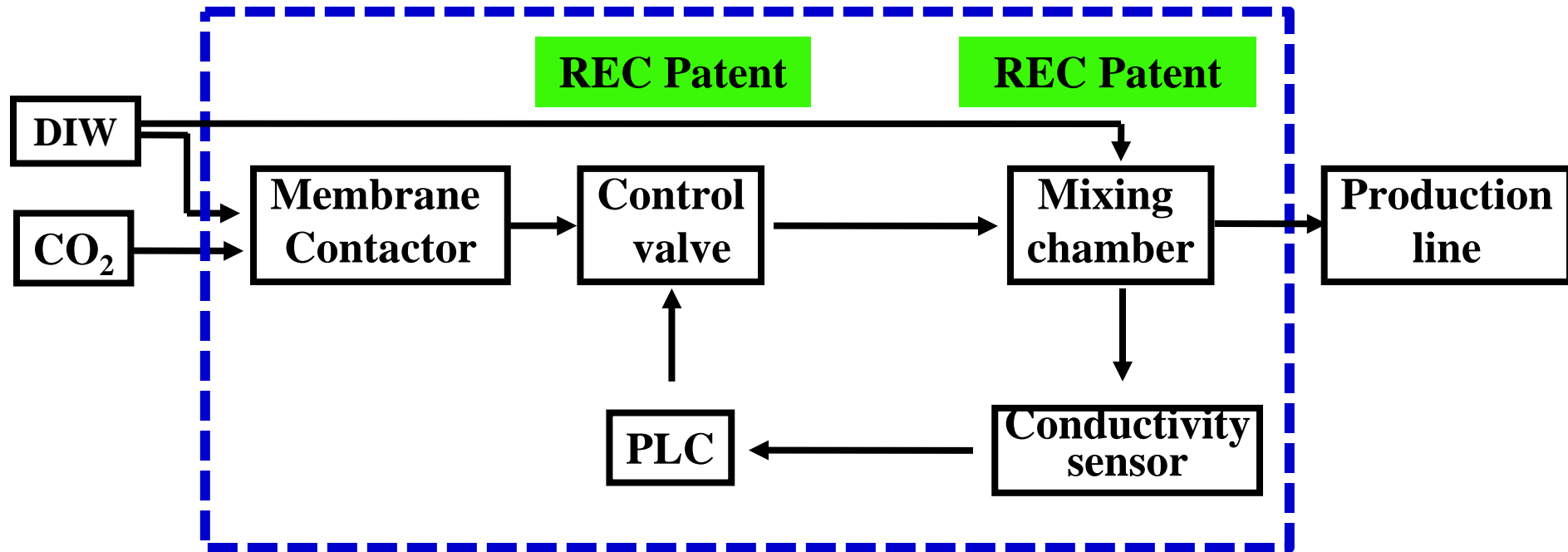
System Design



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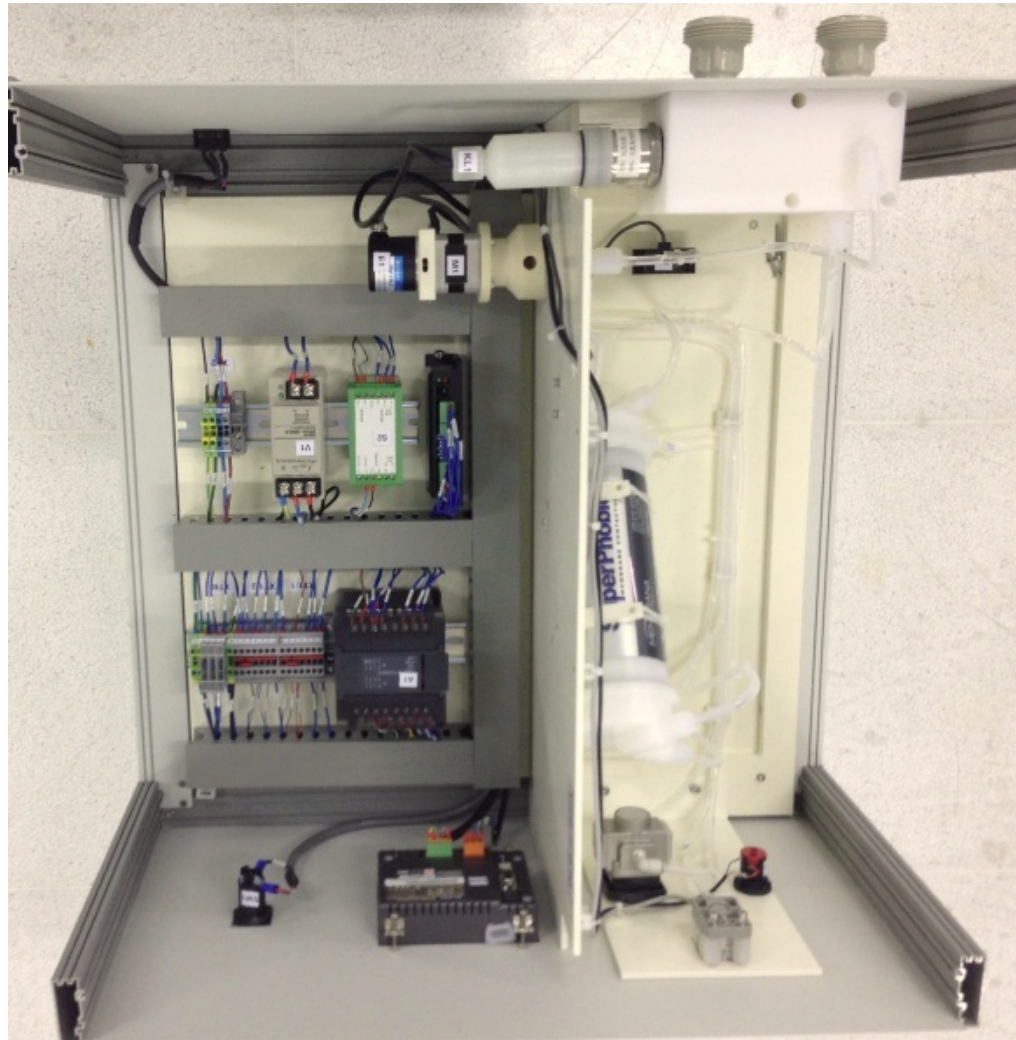
CO₂ & DI mixing



Control Mechanism:

Step motor driven needle valve in the control valve modulates the flow rate of highly concentrated CO₂ water entering the 2nd mixing chamber based on the signal from conductivity sensor

【Top view】

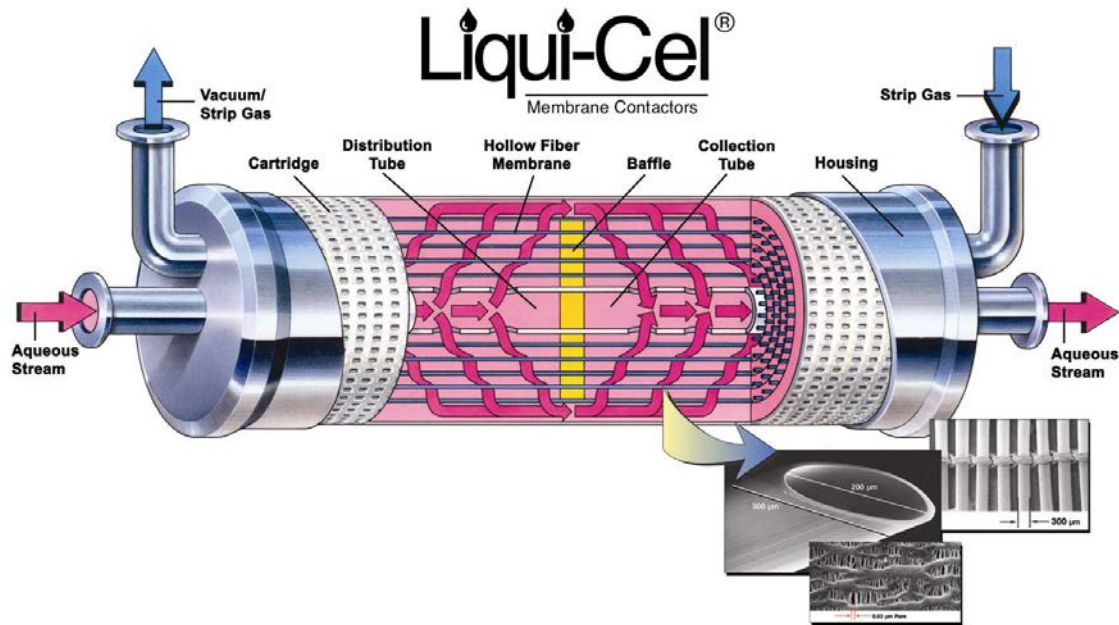


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【Product key technique I】

Gas adding membrane



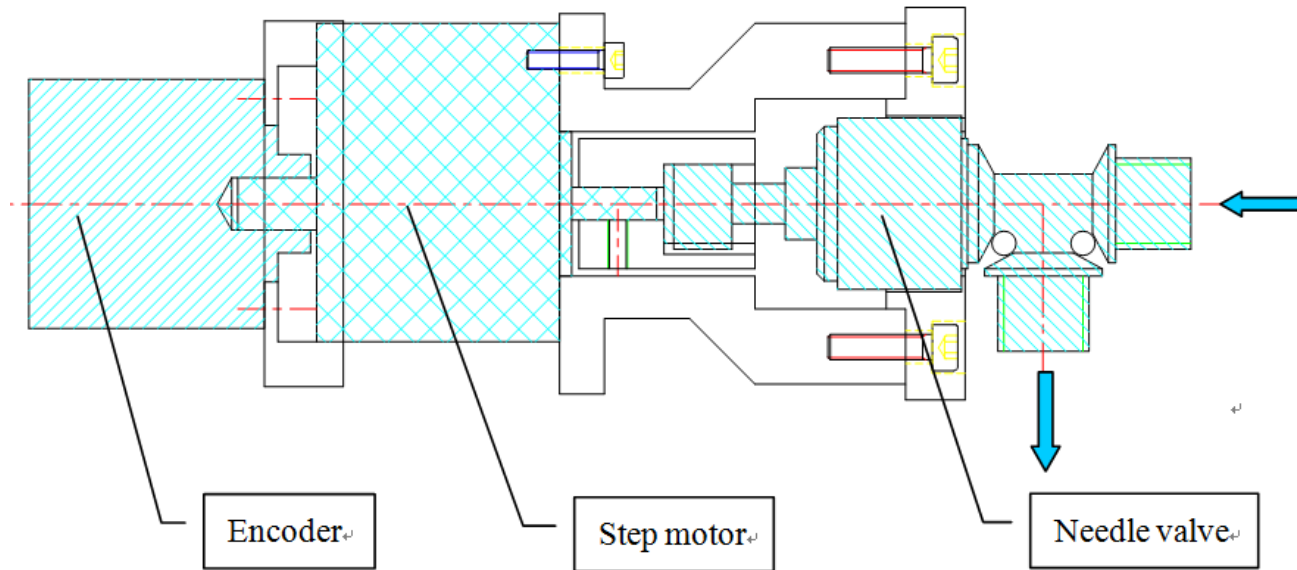
Large surface area membrane produces highly concentrated CO₂ re-ionized water

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【Product key technique II】

Control valve



Step motor driven mechanism precisely control the volume of concentrated CO₂ re-ionized water for 2nd tier mixing

【Product key technique III】

2nd tie mixing chamber



Internal check valve design to prevent down stream water backflow causing contamination on membrane and DI water supply

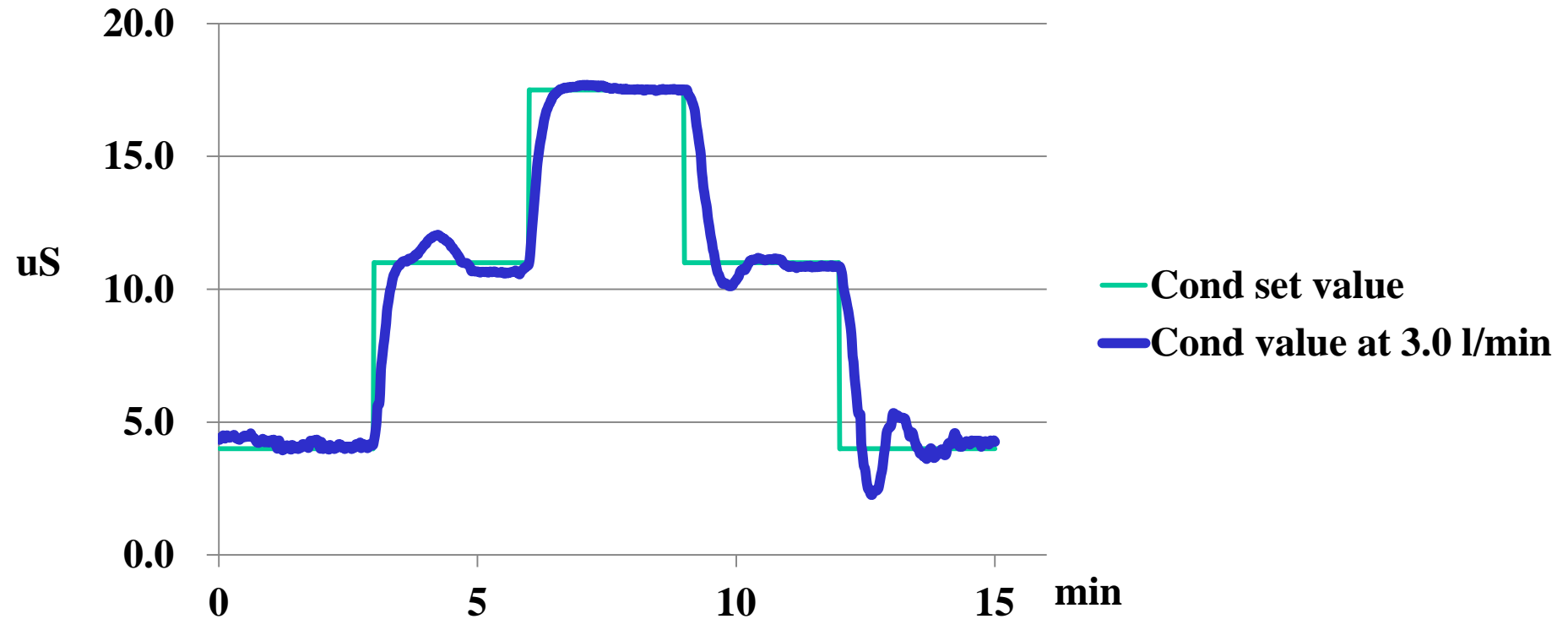
Key techniques



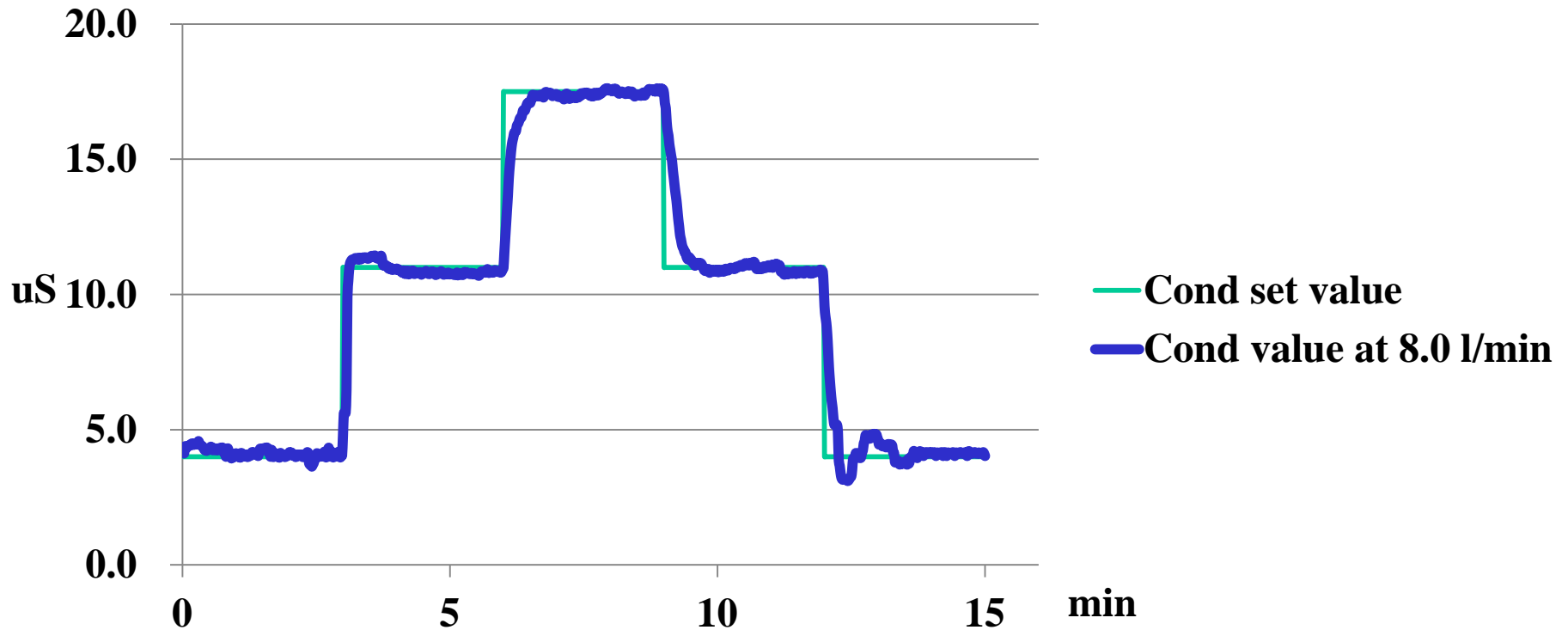
Major advantages

- ① *Large surface area membrane*
 - ② *REC patent feedback loop control mechanism*
 - ③ *REC patent 2nd tier mixing chamber design*
-
- ① *Wide range for DICO₂ flow rate*
 - ② *Precise control for resistivity set point with wide flow rate span*
 - ③ *Fast response for resistivity set point change*

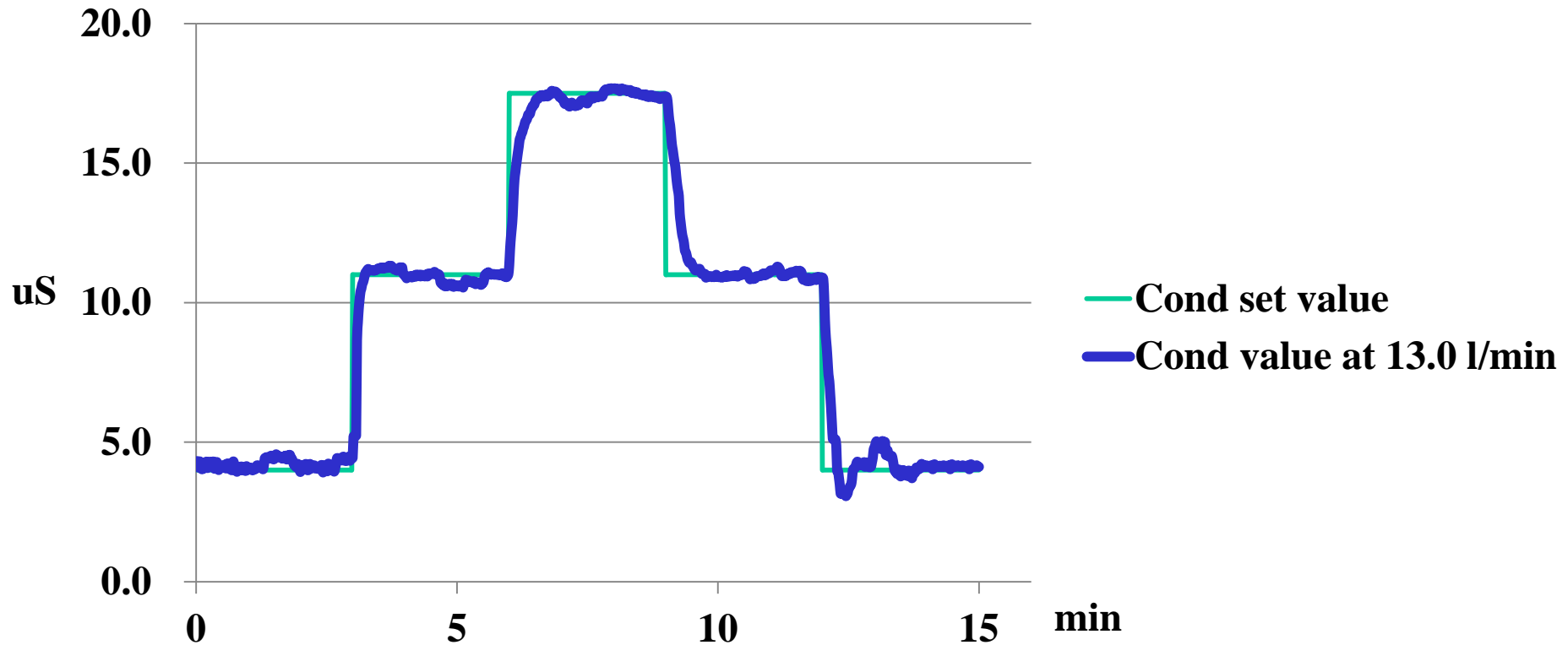
Results



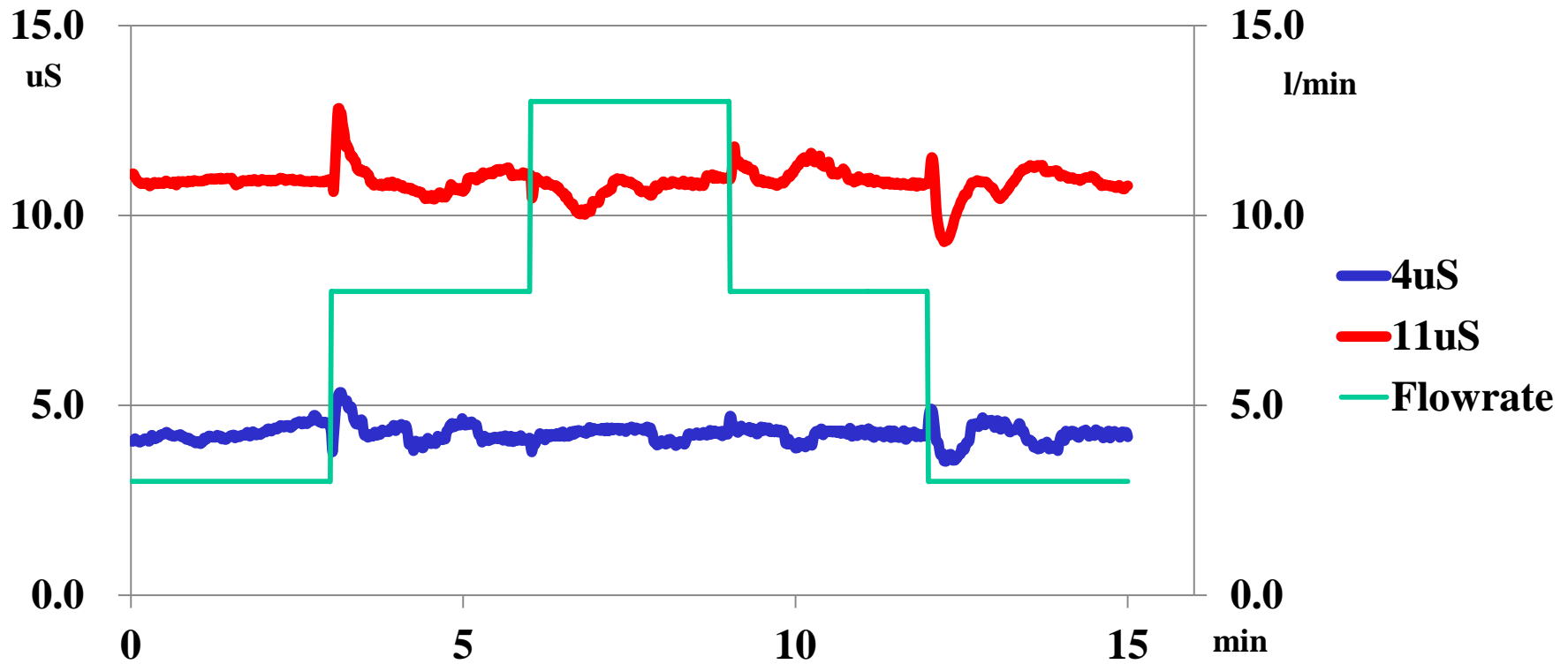
Time to Set Value (+/- 1uS): 15sec~30sec



Time to Set Value (+/- 1uS): 6sec~18sec



Time to Set Value (+/- 1uS): 8sec~21sec



Time to Set Value (+/- 1 μS): 13sec~15sec

Total range: Set value +/- 1.5 μS



Acknowledgements

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Thank You!

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